

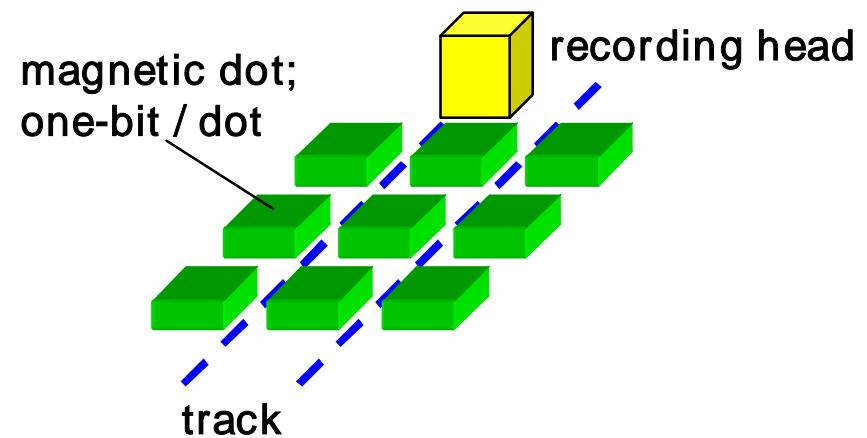
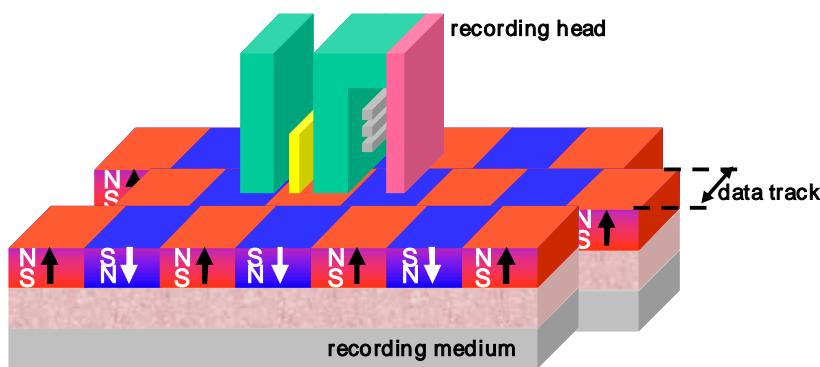
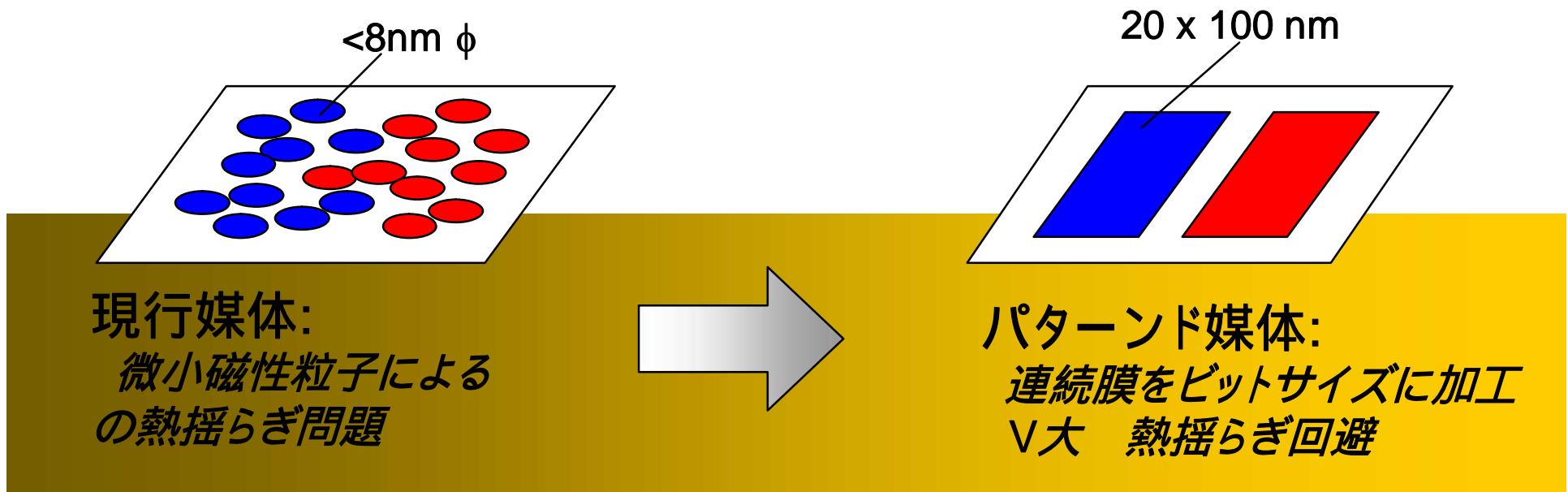


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# ×線反射率法を用いたパターン媒体の 加工ダメージ評価

(株)東芝 研究開発センター  
喜々津 哲

# パターンド媒体のコンセプト



# パターンド媒体の課題

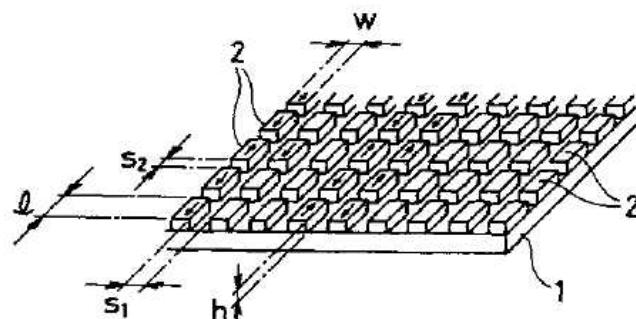
## Challenging Issues

- 製造(加工)方法
- 浮上性能/表面平滑化

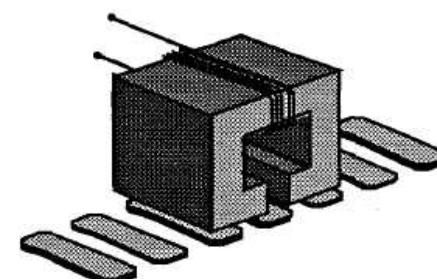
feature size~10nm

## Engineering Issues

- 媒体の磁気特性デザイン
- サーボ、ヘッド位置制御法
- 信号制御、チャネル (ビットに同期した記録)
- ヘッドデザイン



Nakatani: Japanese Pat. (1989)



R. White: IEEE Trans. Magn., 33 p.990 (1997)

# ポリマーの自己組織化を利用した微細パターン

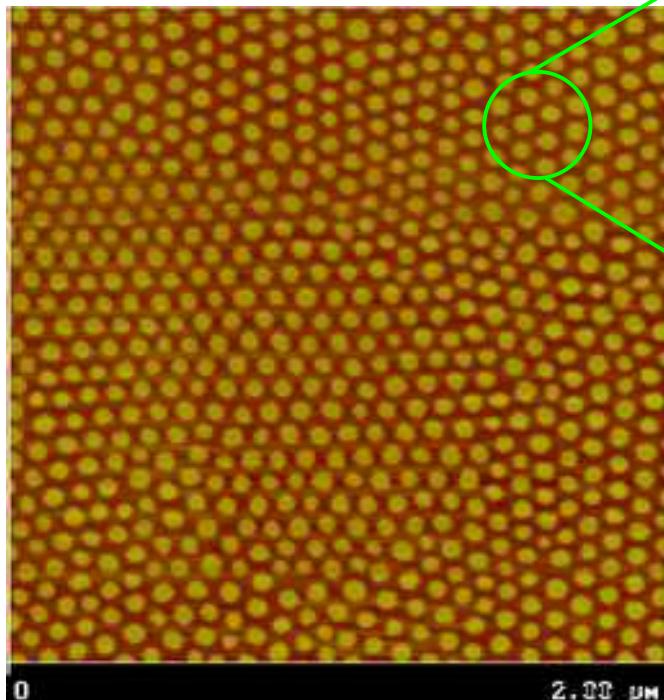
PS-PMMA ジブロックコポリマー(di-block co-polymer)

ポリスチレン (PS)  
(分子量: 172000)

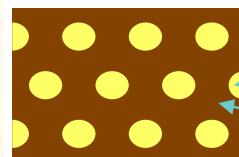
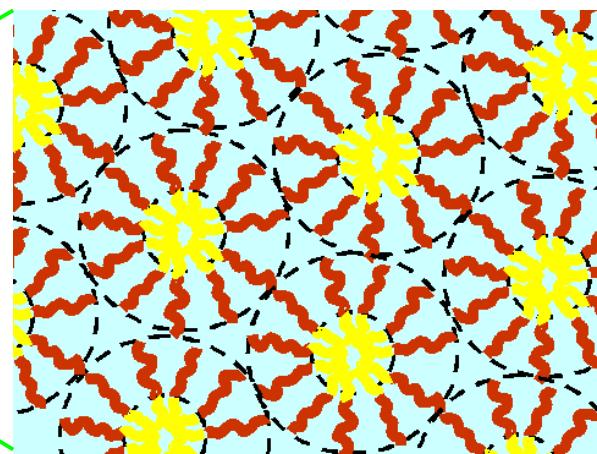


ポリメチルメタクリレート(PMMA)  
(分子量: 41500)

AFM 位相像



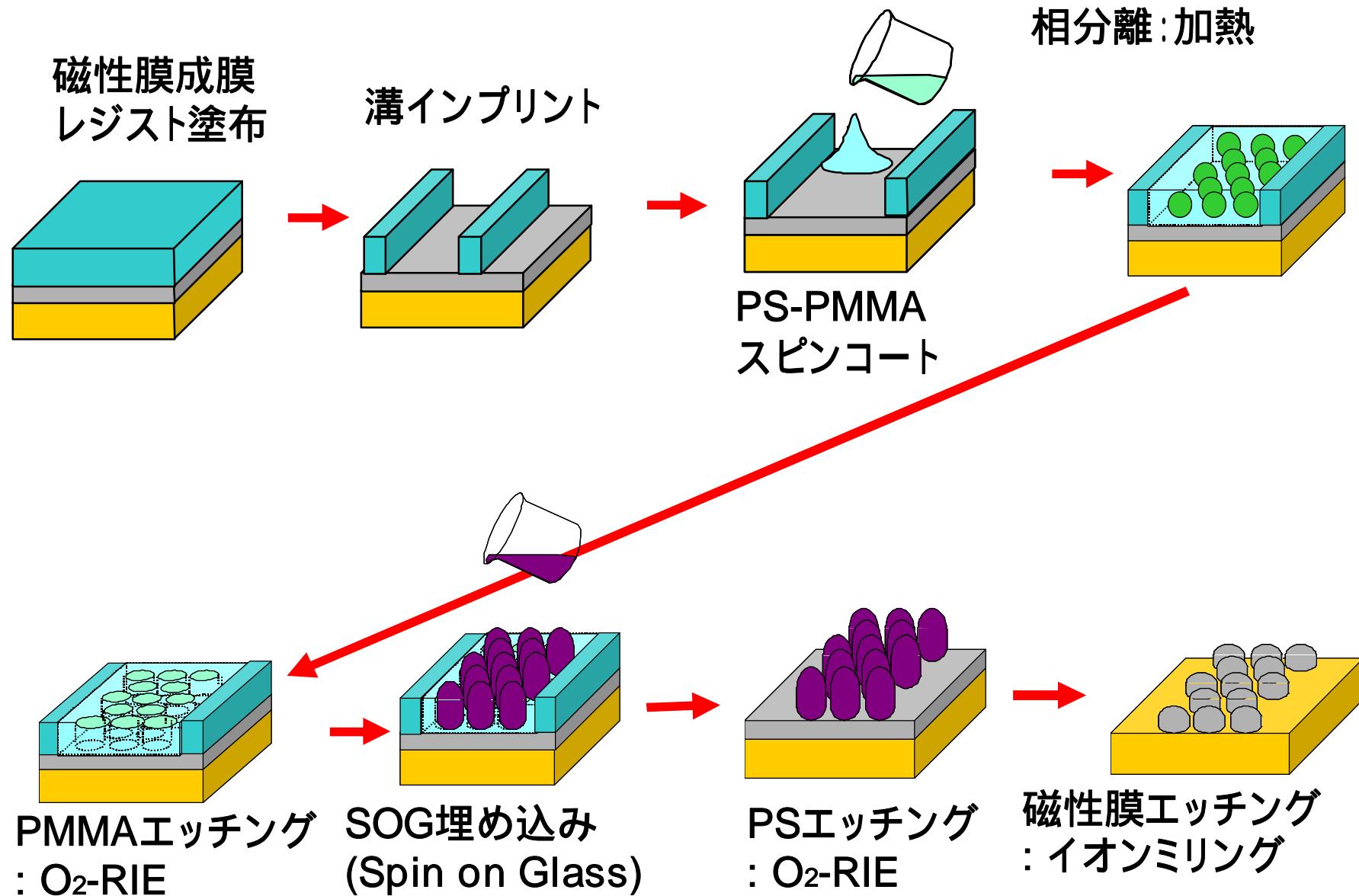
80 nm間隔, 40nm直径



## 自己組織化

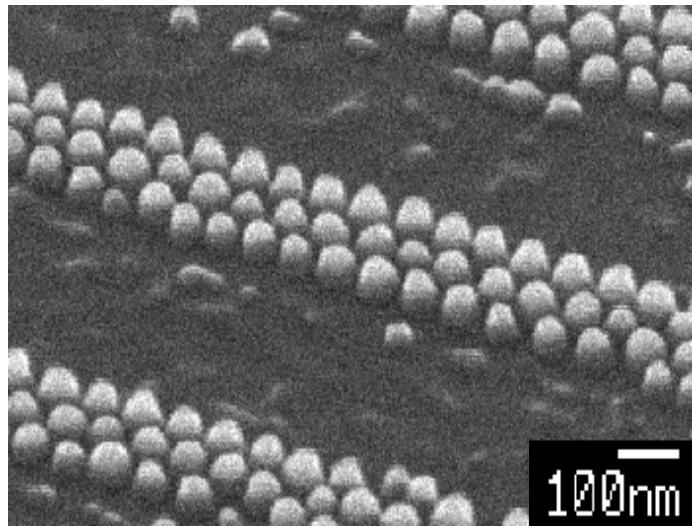
- ・大面積のナノ構造を一度に形成
- ・~10nmも可

# パターンド媒体形成プロセス



# CoCrPtパターンド媒体

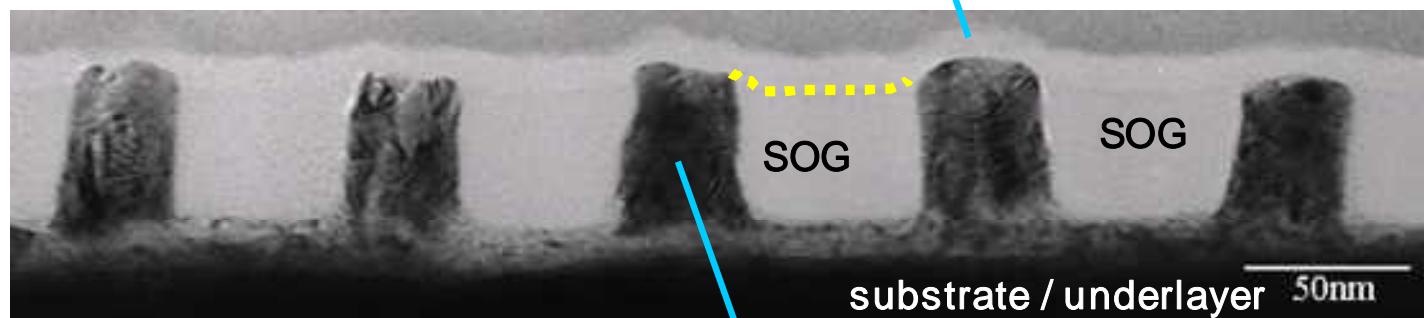
Co<sub>74</sub>Cr<sub>6</sub>Pt<sub>20</sub>パターンド媒体(80 nmピッチ、40 nm直径)



SEM像

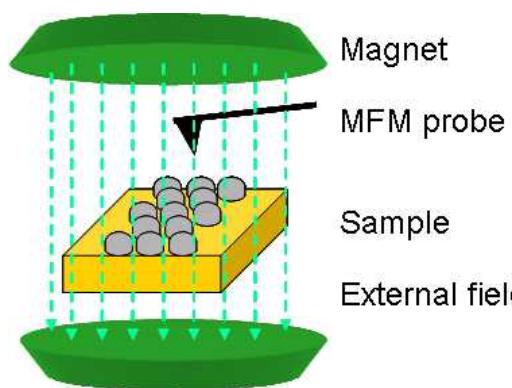


C保護膜  
全体像

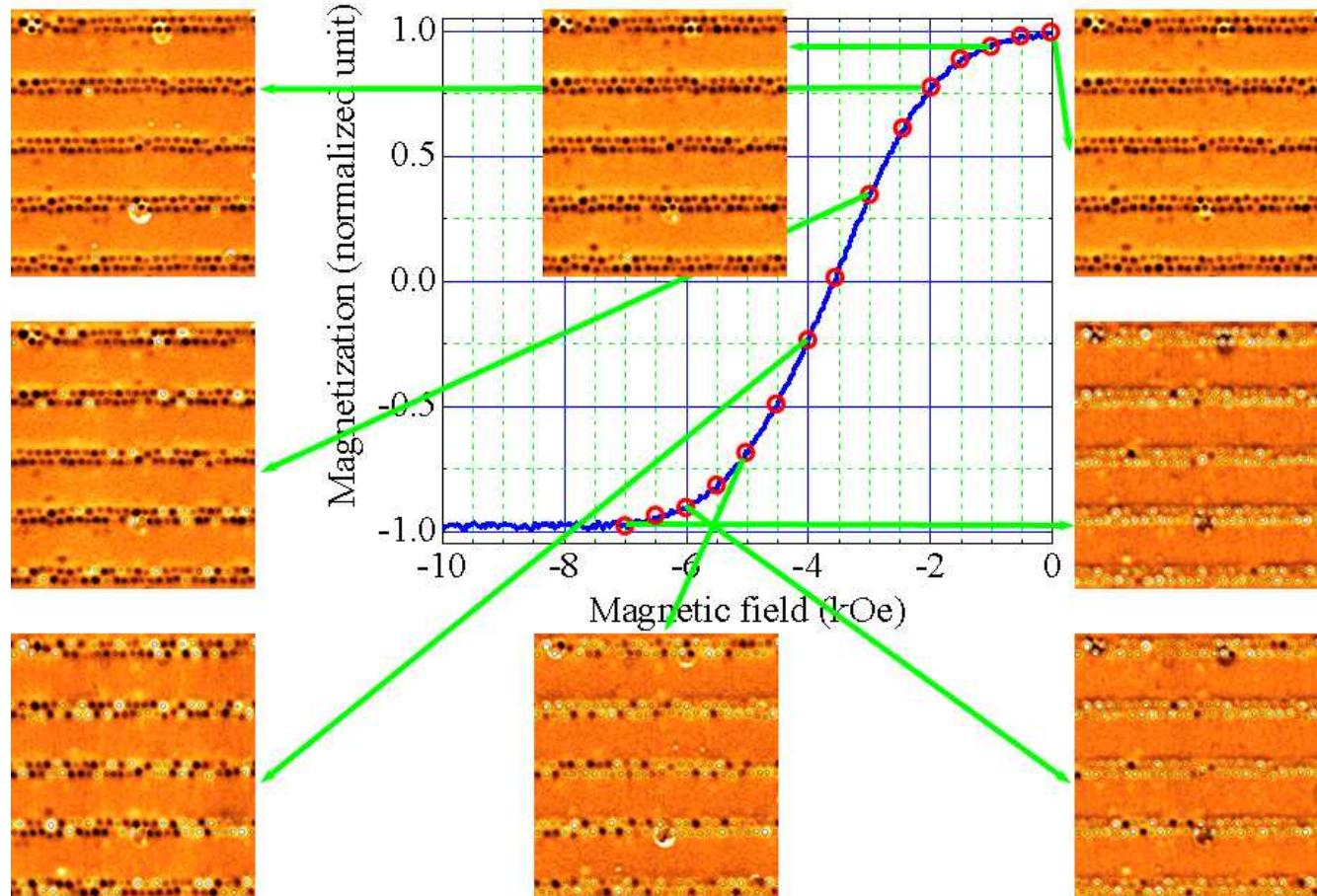


Y. Kamata: Intermag06 GE-09

# MFMを使ったドット毎の磁気特性測定



磁界印加 MFM測定

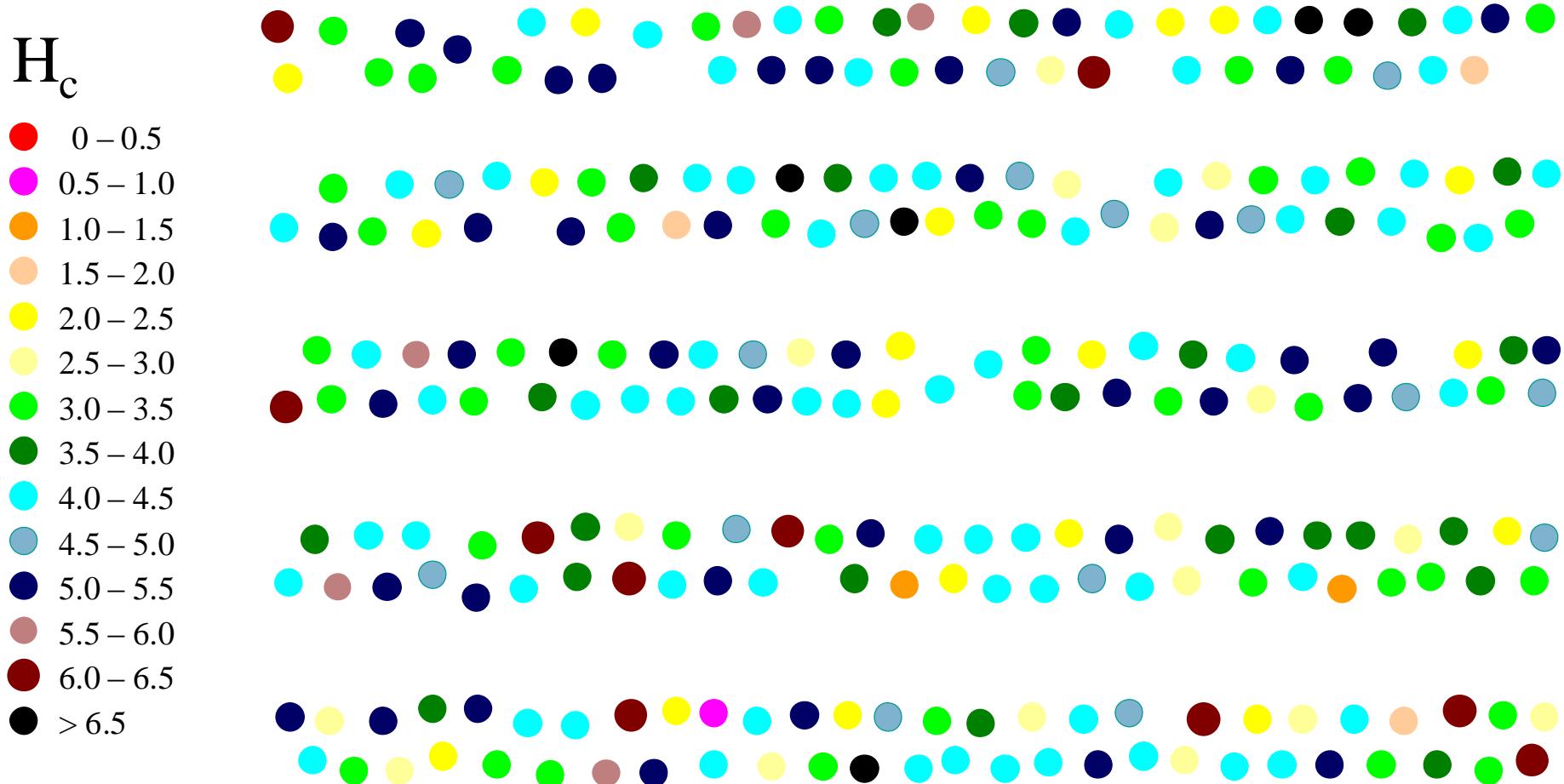


反転したドット個数を数える = 磁化量

J.Bai et al., J. Appl. Phys., Vol.96, No.2, 1133(2004).

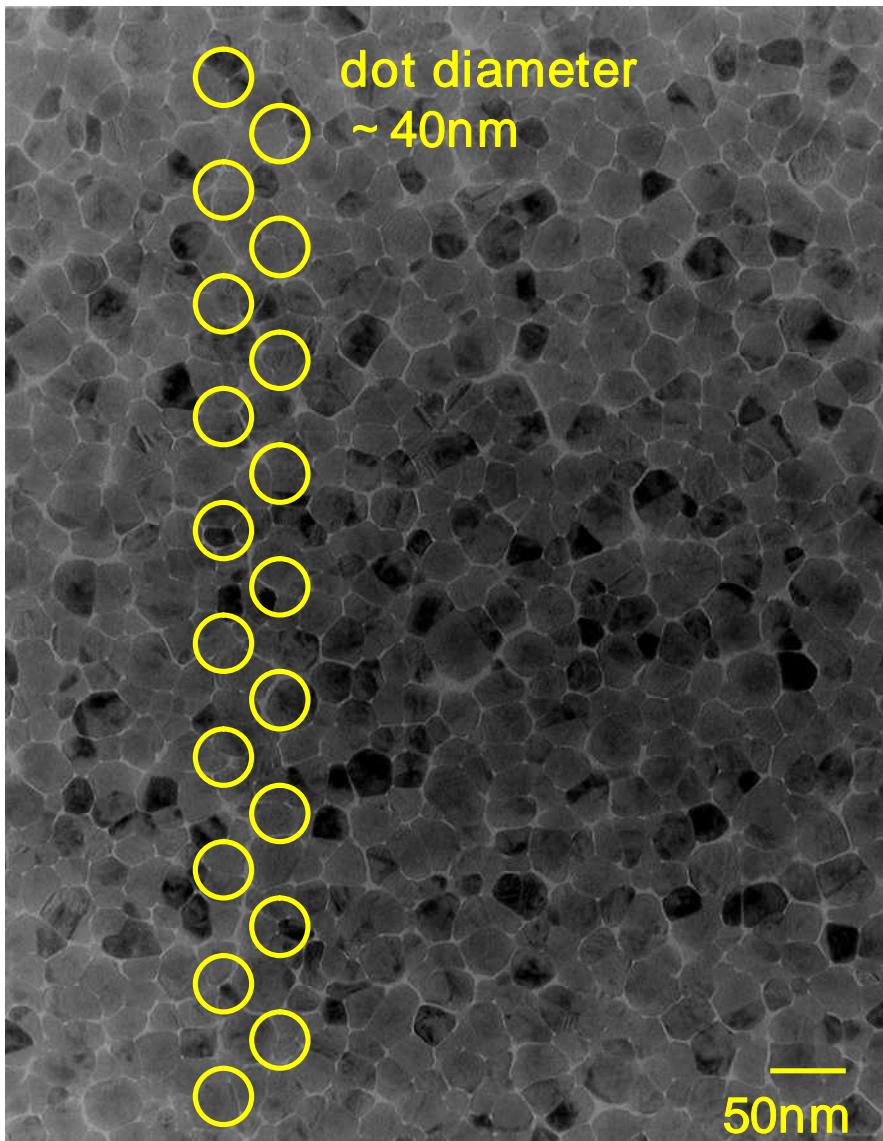
# 各ドットの保磁力分布

Hc distribution of aligned CoCrPt dots (40nm $\phi$ )

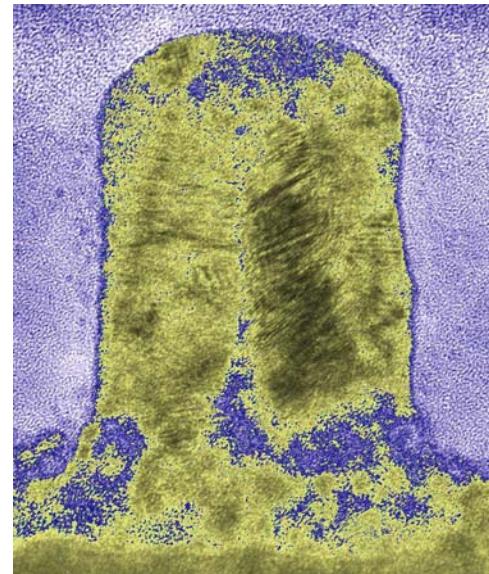


Y. Kamata: Intermag 06 GE-09

# ドットの均一性: 数本の粒界、異方性軸分布

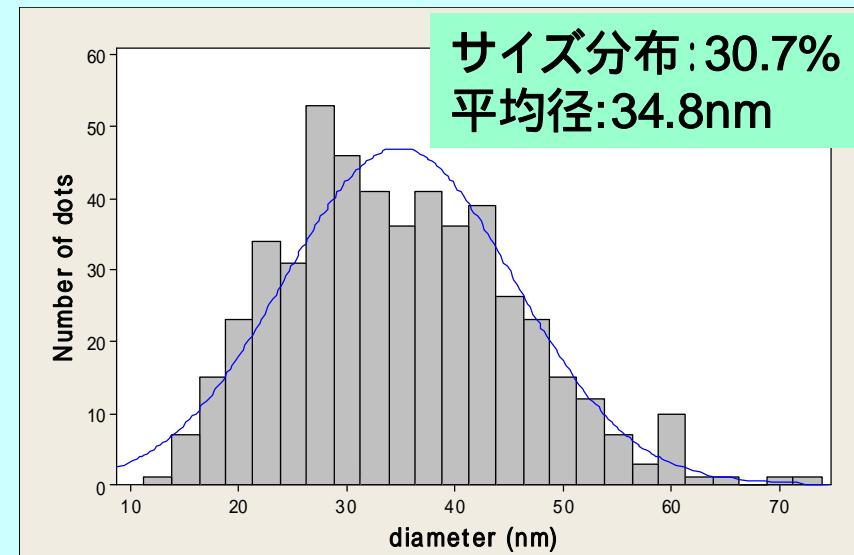
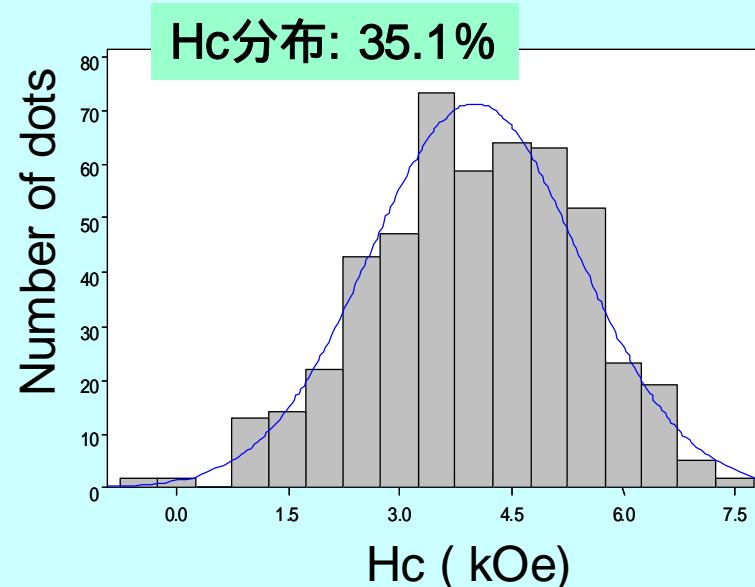


磁性膜の平均粒径: 22.9 nm  
パターンサイズ: 40 nm  
ドット中に粒界が1-2個



端っこにあると熱揺らぎ  
垂直配向軸のばらつき、

# 磁気特性分布の原因



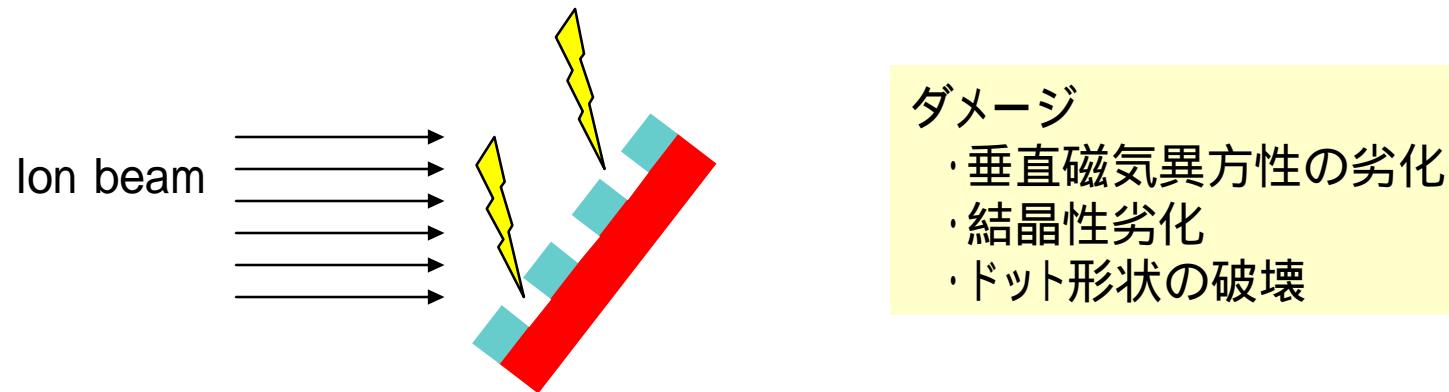
Y. Kamata: JJAP Vol.40, No.3A, 999(2007)

## possible origin of the distribution

- dot size distribution
- microscopic composition dispersion
- grain boundary
- damage by the etching process
  - ... TEM, simulation: little damage by ion milling

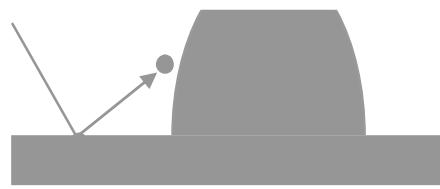
# Arイオンミリングプロセス

利点: どのような磁性膜でもエッチングできる  
欠点: エッティングダメージ



redeposition: 再付着

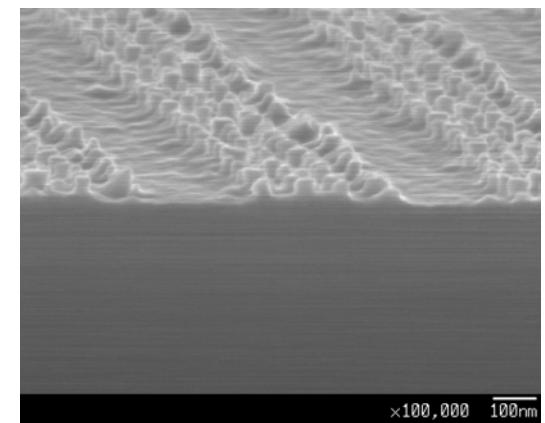
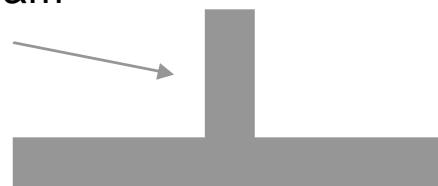
Ion beam



Back sputtering

sidewall etching: サイドエッチ

Ion beam

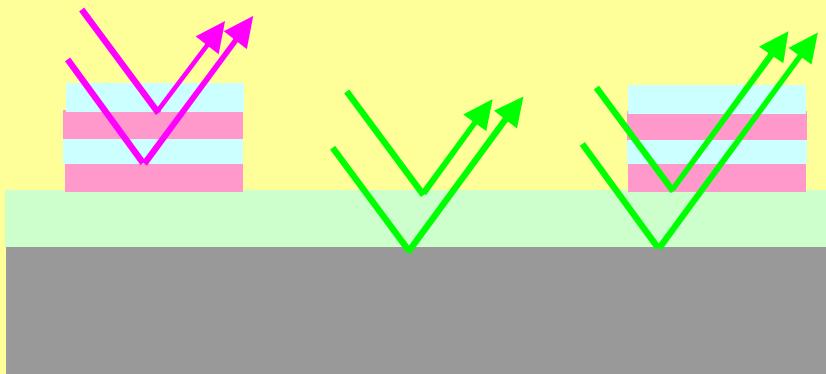


## introduction (II)

### motivation:

etching damage analysis of the patterned media  
made by ion milling process with self assembled mask

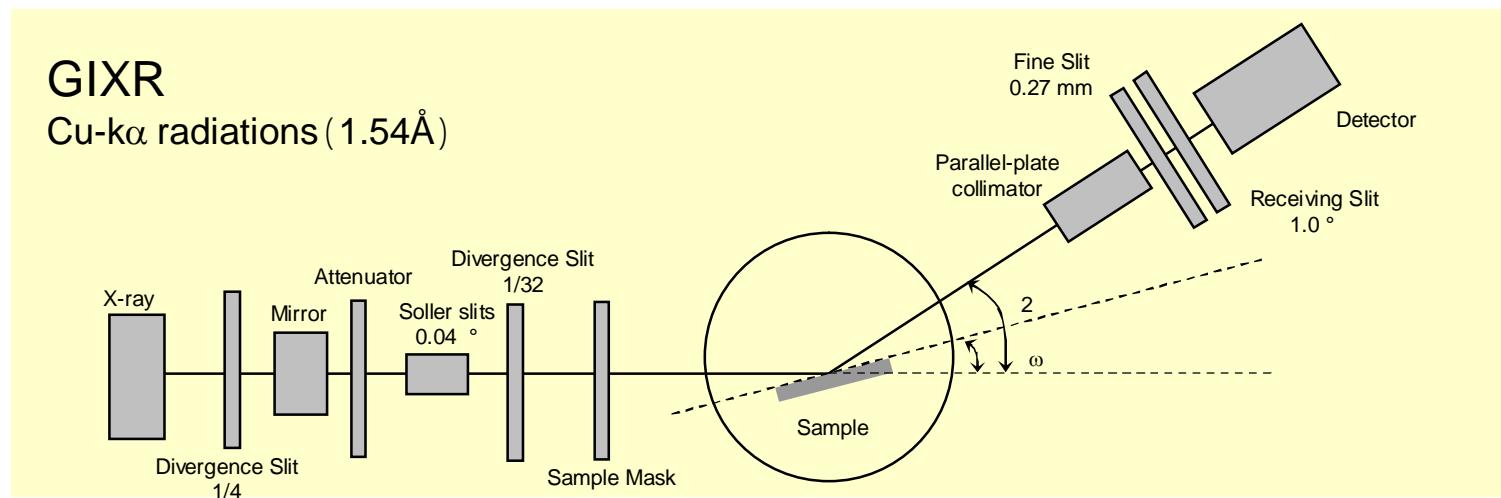
- magnetic layer: Co/Pt multilayer
  - magnetic properties by multilayer structure
  - sensitive to the physical damage
- method: **Grazing Incidence X-ray Reflectivity (GIXR)**
  - layer structure, roughness



similar refraction is expected;  
multilayer: reduced intensity  
underlayer: increased intensity  
dot edge: scattering

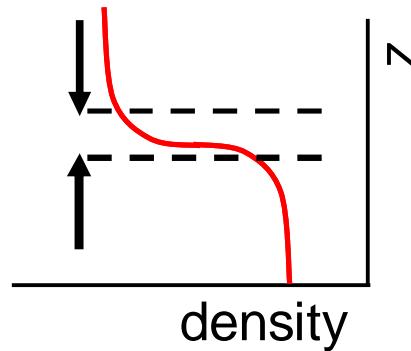
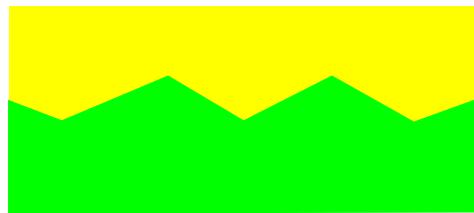
# experiment - measurement

- saturation magnetization ( $M_s$ ): VSM
- magnetic anisotropy energy ( $K_u$ ): VSM, torque meter
- crystalline structure: XRD
- thickness and roughness: GIXR
- microstructure: TEM



# Fitting model; roughness

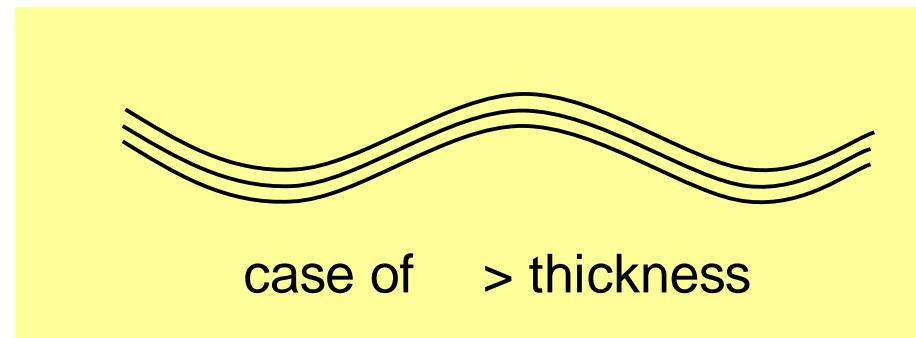
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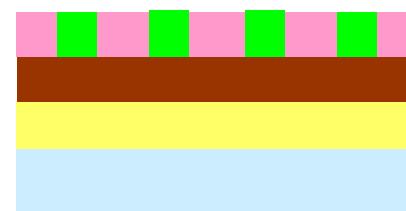
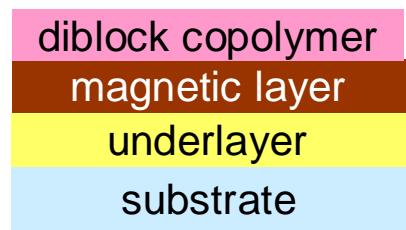
rough interface → gradual density change:  $\rho(z)$   
 $\rho(z)$ : error function

$$\rho(z) = \frac{1}{\sqrt{\pi}} \int_{-\infty}^z \exp\left(-\frac{t^2}{2\sigma^2}\right) \cdot dt$$

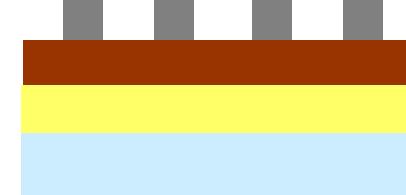
: roughness



# experiment – fabrication process



phase separation

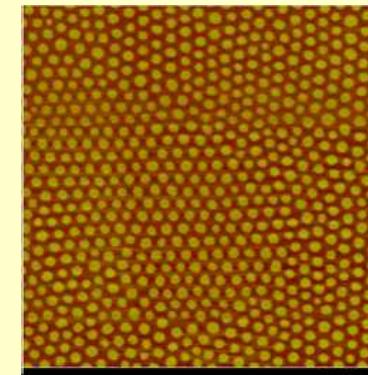


O<sub>2</sub> RIE  
SOG substitution

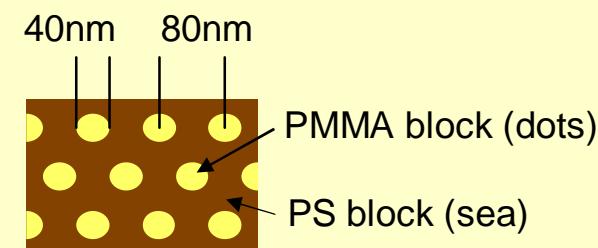


Ar ion milling  
CF<sub>4</sub> RIE

PS-PMMA diblock copolymer

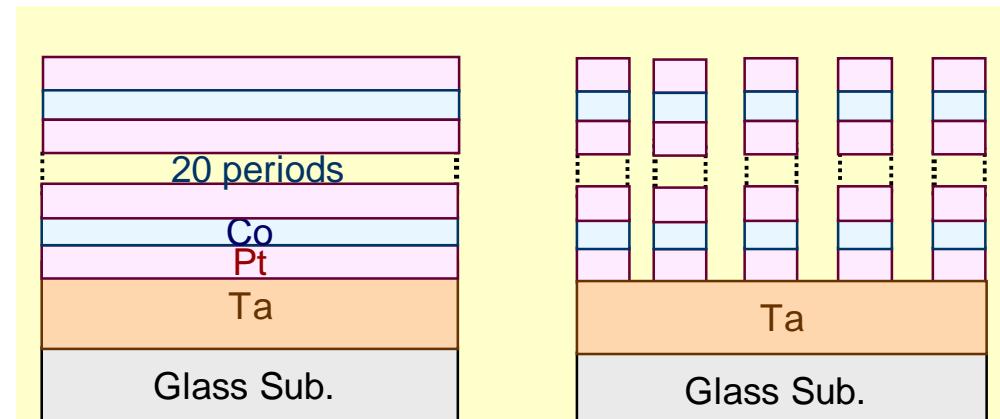
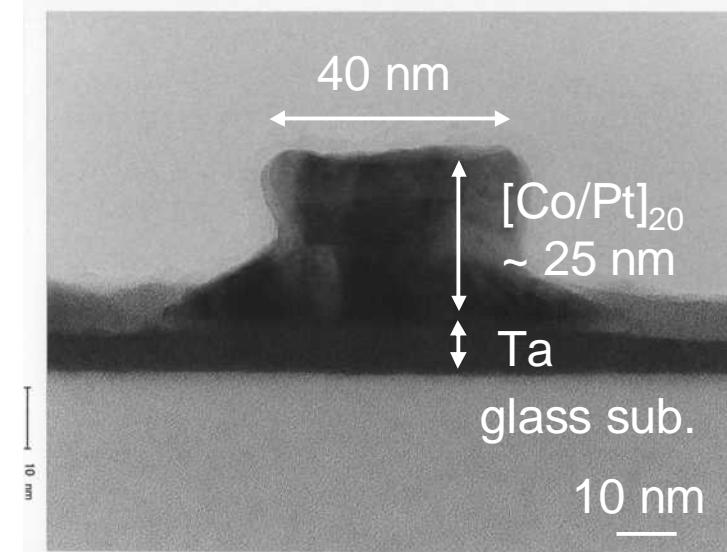
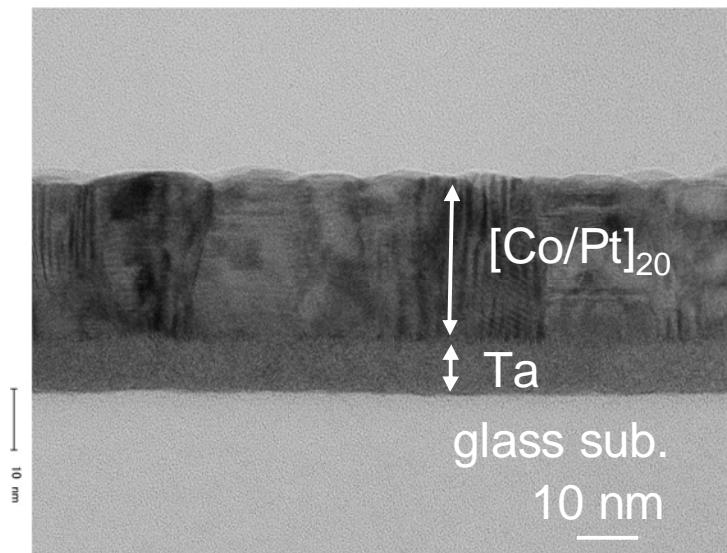


AFM



K. Naito et.al.: IEEE Trans.Magn. 38, 1949 (2002)

# Co/Pt multilayer sample



Before Etching

After Etching

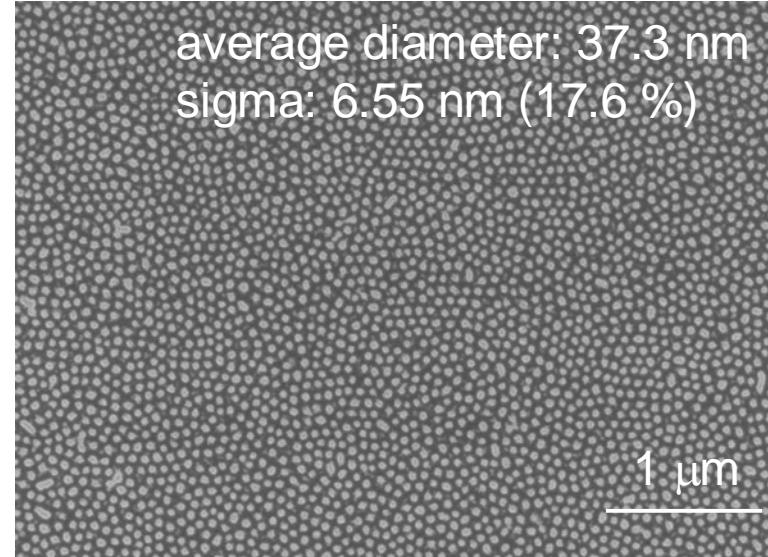
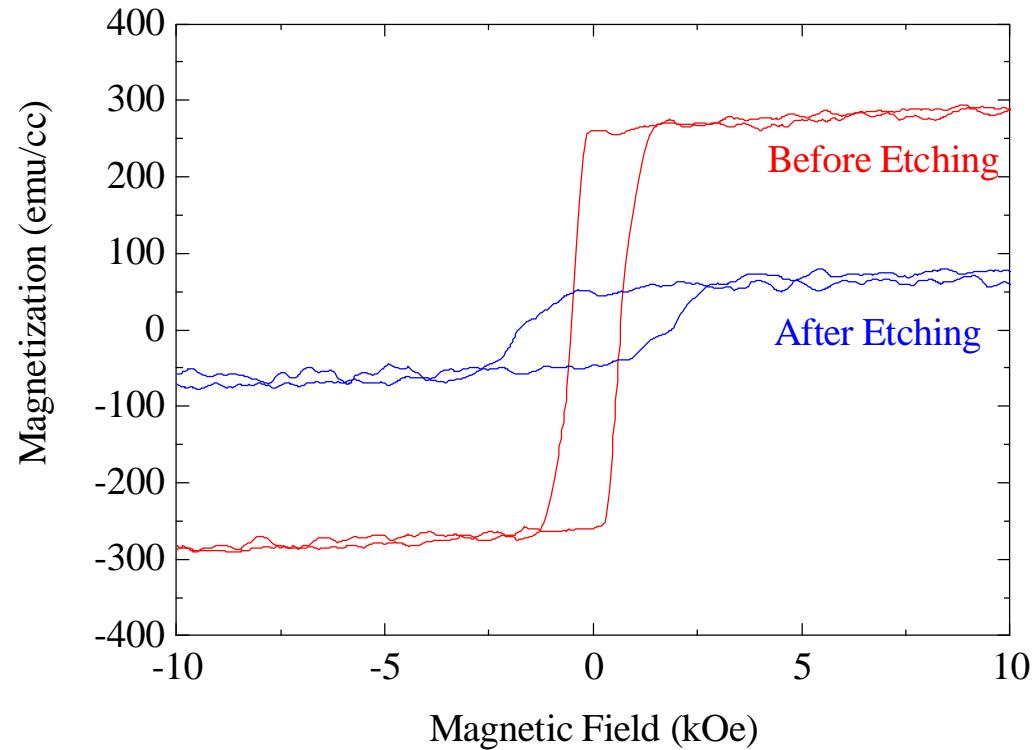
## ➤ Sputtering condition

Co: 0.3nm, Pt: 0.9nm  
DC sputtering  
no substrate heating  
Ar pressure: 0.5 Pa

## ➤ Milling condition

substrate cooling  
accelerating voltage : 400 eV  
Ar pressure :  $2.5 \times 10^{-4}$  Torr  
etching angle : 30 deg.

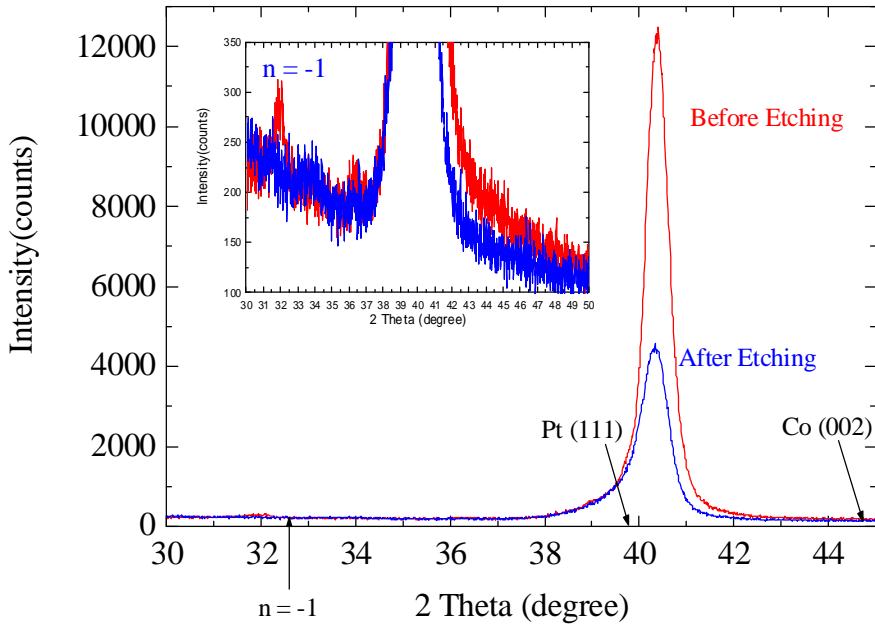
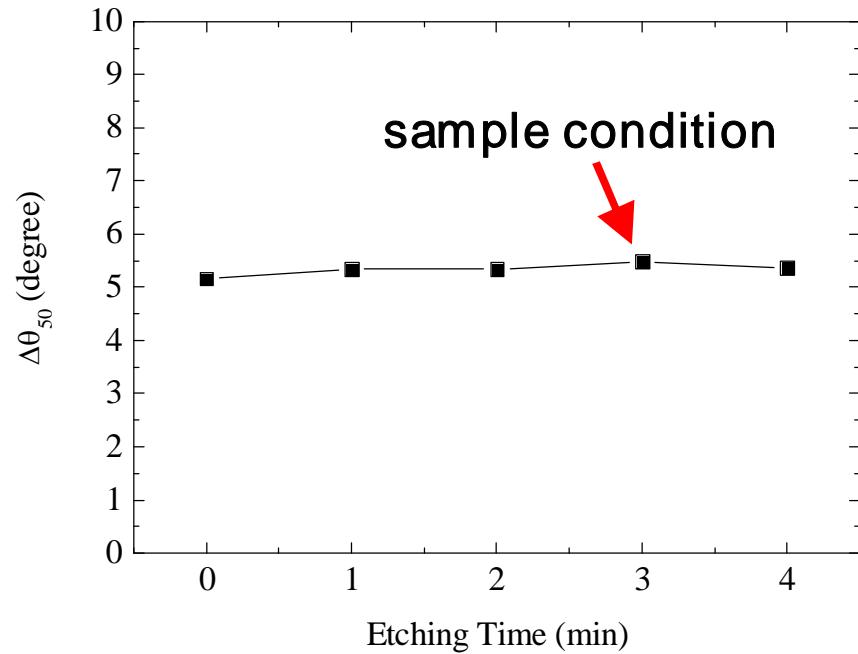
# magnetic properties



little damage to the magnetic properties

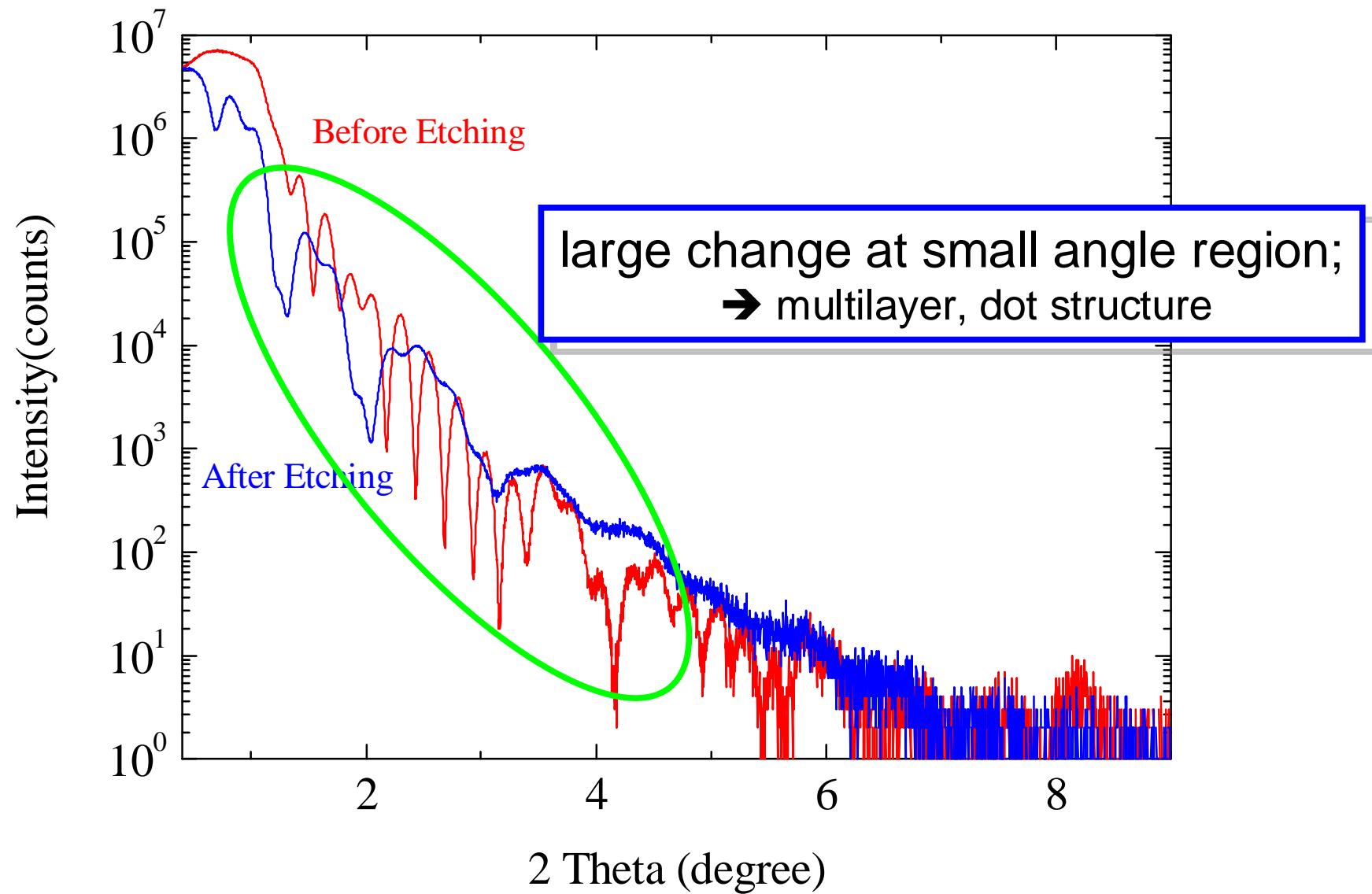
- reduction in  $M_s$ : proportional to the packing density
- $K_u$  (by torque curve amplitude): no change

# crystal properties (XRD: $\theta$ - $2\theta$ )

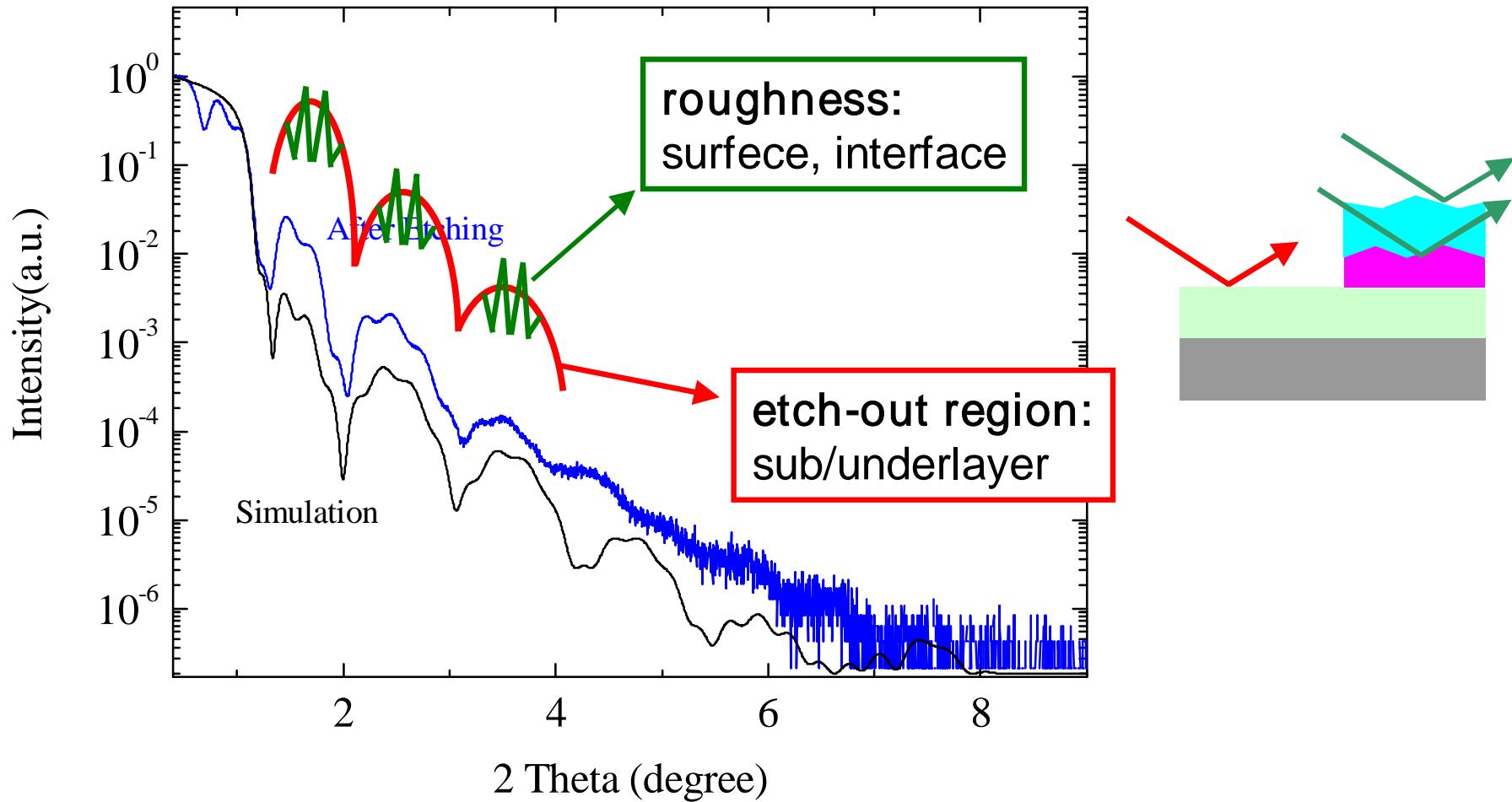


- $\Delta\theta_{50}$ : little change throughout the etching process
- $\theta$ - $2\theta$ :
  - reduced intensity by volume reduction
  - before etching: satellite peak from multilayer structure
  - **after etching: no satellite peak → damage?**

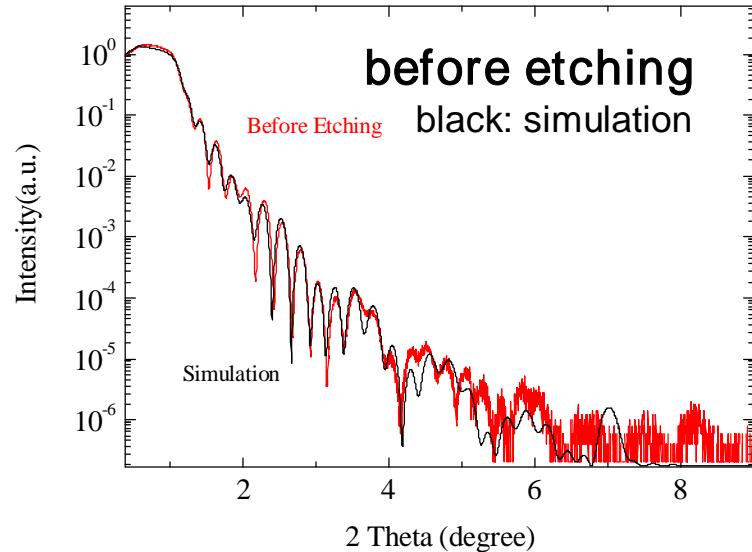
# X-ray reflection profile



# profile details (after etching)

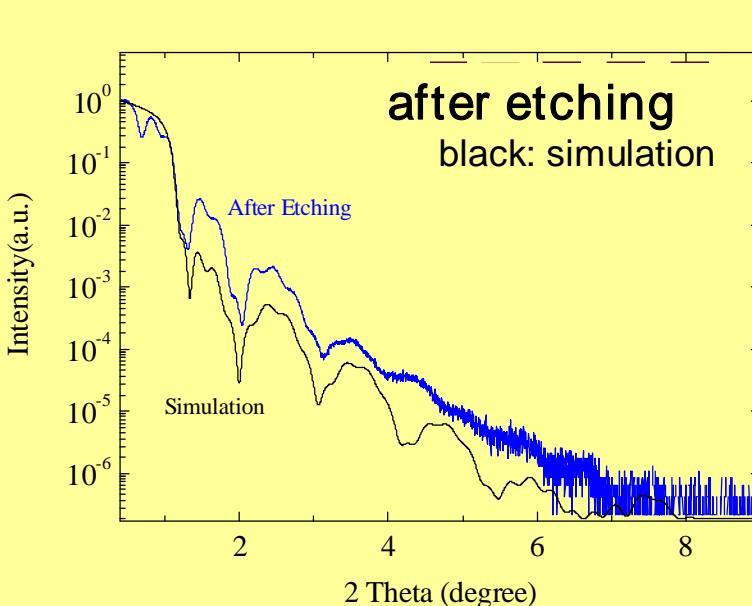


# fitting results



	Nominal thickness (nm)	Fitting thickness (nm)	Roughness (nm)
Top Pt	0.9	0.90	0.90
$[Co/Pt]_{20}$	0.3/0.9	0.37/0.90	0.45/0.90
Ta	8.0	7.45	0.50
Glass Sub.			0.5

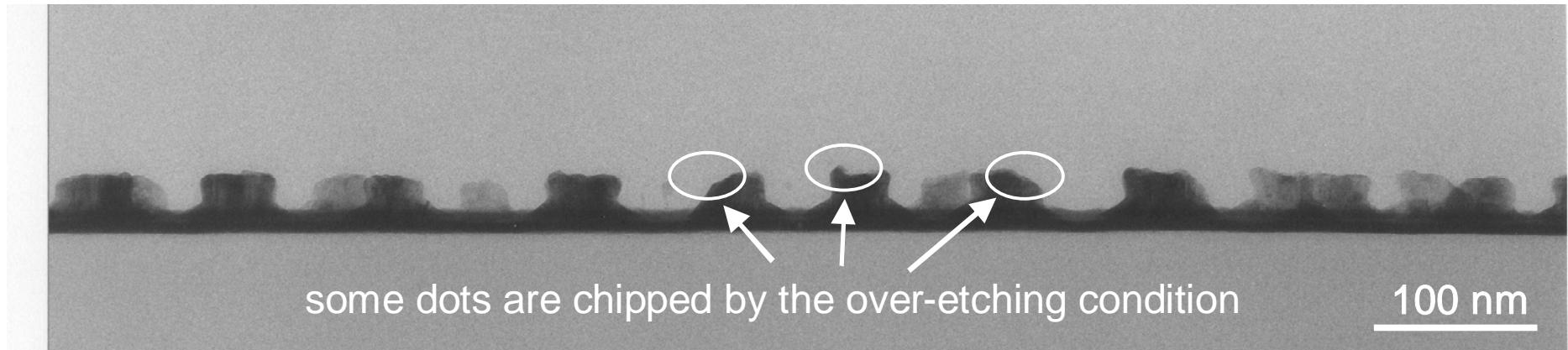
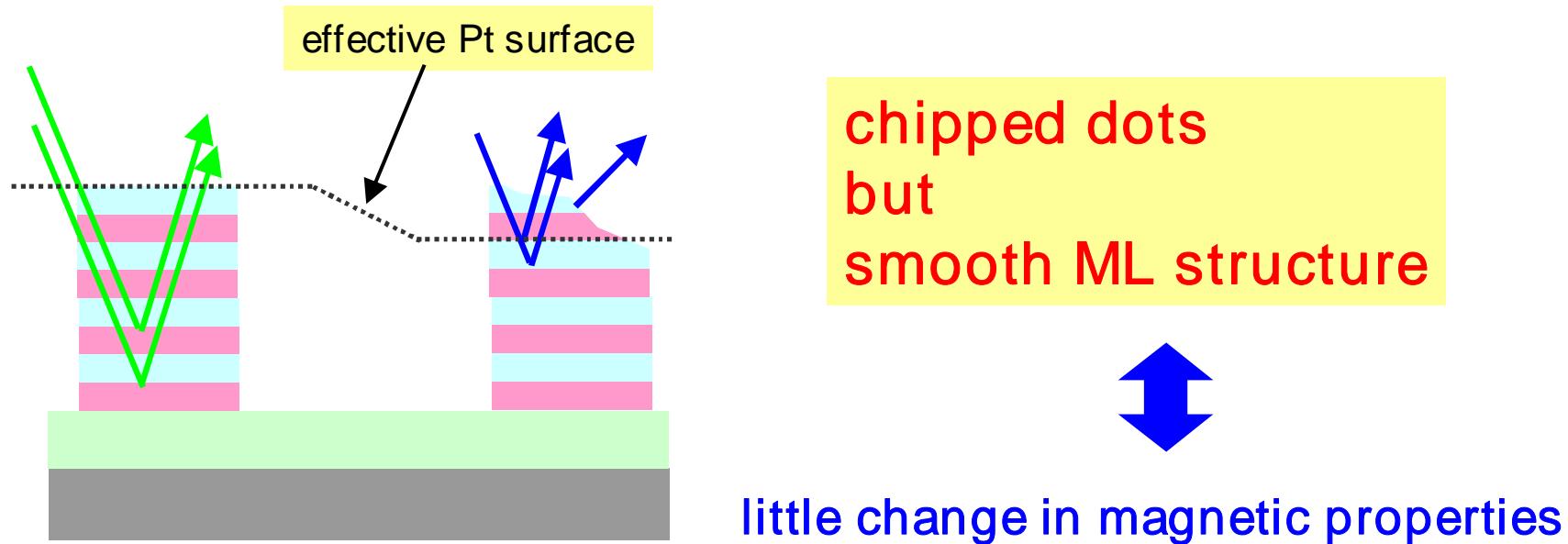
- good agreement with nominal thickness
- roughness  $\sim 1\text{nm}$  at  $[Co/Pt]$  and top



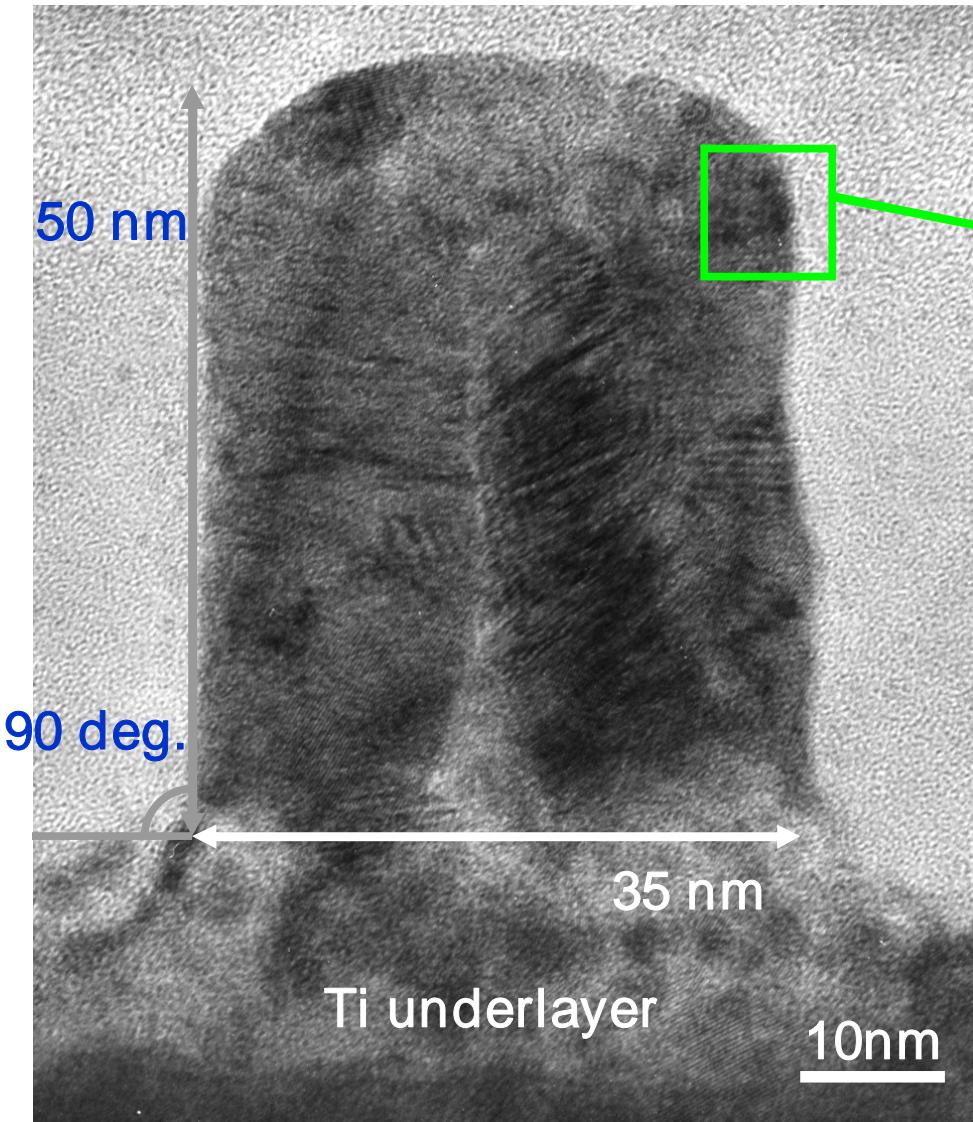
	Nominal thickness (nm)	Fitting thickness (nm)	Roughness (nm)
Top Pt	0.9	0.80	3.80
$[Co/Pt]_{20}$	0.3/0.9	0.38/0.80	0.45/0.90
Ta	8.0	7.40	0.55
Glass Sub.			0.5

- little change in ML structure (roughness)
- large roughness at the top Pt layer

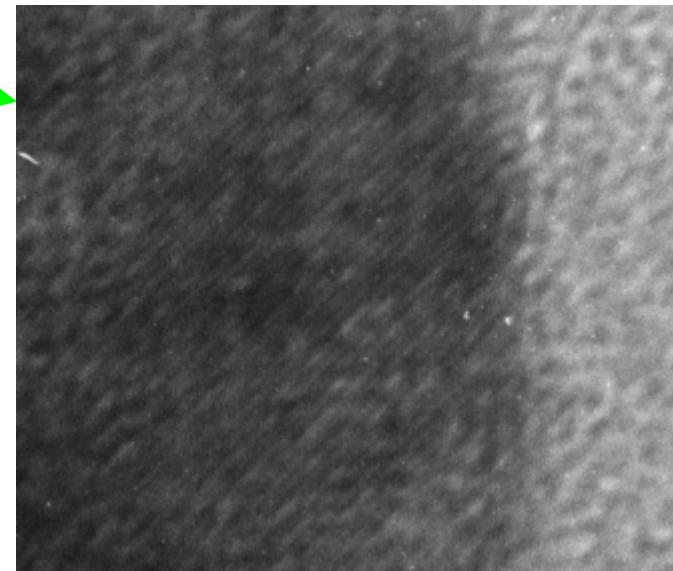
# origin of the large surface roughness



## CoPt合金の例: サイドダメージは少ない



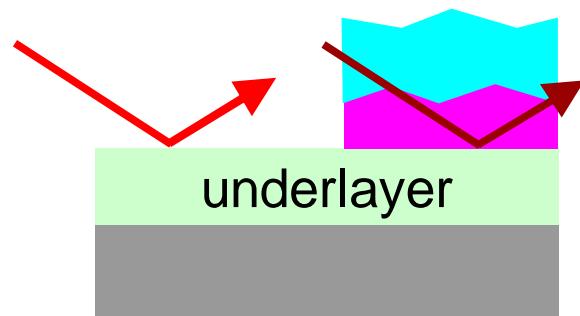
clear crystalline lattice:  
no damage



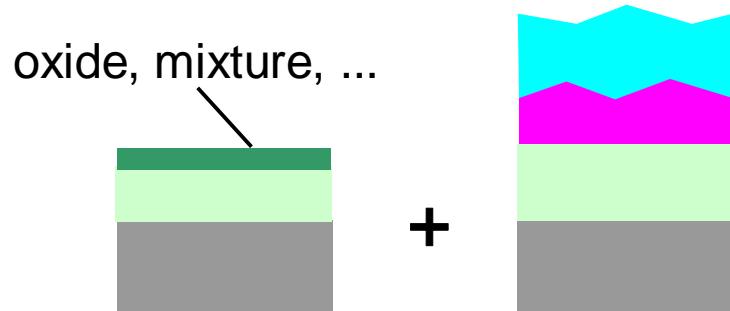
Etching angle : 30 deg.  
Etching time : 8 min.

# for further precise estimation

Issue: strong reflection from the etched-out region



difference in reflectivity of underlayer  
between etch-out region and dot region  
→ Analytical estimation is difficult.



Summation of two spectra  
(or subtraction) could work well.

# conclusion

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## Grazing Incidence X-ray reflection method for etching damage analysis of BPM

- Co/Pt multilayer patterned media:  
**large surface roughness with smooth ML structure**  
chipping by the over-etching condition  
smooth ML  $\Leftrightarrow$  little damage of magnetic properties
- **ion milling process causes less damage**
- **issues for precise estimation**  
;strong reflection from reside underlayer